

Nizami Gasanly

List of Publications by Year in descending order

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189
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| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Defect assisted nonlinear absorption and optical limiting in amorphous $\text{TlGaS}_2(1-x)\text{Se}_2(x)$ ($0 \leq x \leq 1$) thin films. <i>Journal of Luminescence</i> , 2022, 241, 118540. | 3.1 | 13 |
| 2 | Effect of temperature on band gap of PbWO_4 single crystals grown by Czochralski method. <i>Physica Scripta</i> , 2022, 97, 045803. | 2.5 | 8 |
| 3 | Temperature-dependent optical characteristics of sputtered NiO thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2022, 128, 1. | 2.3 | 11 |
| 4 | Temperature-tuned bandgap characteristics of Bi_2TiO_7 sillenite single crystals. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 1316-1322. | 2.2 | 5 |
| 5 | Optical and Nanomechanical Properties of Ga_2Se_3 Single Crystals and Thin Films. <i>Jom</i> , 2021, 73, 558-565. | 1.9 | 2 |
| 6 | Spectroscopic ellipsometry study of Bi_2TiO_7 single crystals. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 7019-7025. | 2.2 | 7 |
| 7 | Structural and temperature-tuned bandgap characteristics of thermally evaporated In_2S_3 thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 15851-15856. | 2.2 | 6 |
| 8 | The effect of Zn concentration on the structural and optical properties of $\text{Cd}_{1-x}\text{Zn}_x\text{S}$ nanostructured thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 25225-25233. | 2.2 | 2 |
| 9 | Investigation of defect levels in $\text{Bi}_{12}\text{SiO}_{20}$ single crystals by thermally stimulated current measurements. <i>Physica Scripta</i> , 2021, 96, 125875. | 2.5 | 0 |
| 10 | Synthesis and temperature-tuned band gap characteristics of magnetron sputtered ZnTe thin films. <i>Physica B: Condensed Matter</i> , 2020, 582, 411968. | 2.7 | 18 |
| 11 | Material and device properties of Si-based $\text{Cu}_{0.5}\text{Ag}_{0.5}\text{InSe}_2$ thin-film heterojunction diode. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 1566-1573. | 2.2 | 2 |
| 12 | Vibrational modes in $(\text{TlGaS}_2)_x(\text{TlGaSe}_2)_{1-x}$ mixed crystals by Raman measurements: compositional dependence of the mode frequencies and line-shapes. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 14330-14335. | 2.2 | 6 |
| 13 | Influence of temperature on optical properties of electron-beam-evaporated ZnSe thin film. <i>Physica Scripta</i> , 2020, 95, 075804. | 2.5 | 5 |
| 14 | Optical constants and critical point energies of $(\text{AgInSe}_2)_{0.75}(\text{In}_2\text{Se}_3)_{0.25}$ single crystals. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 4702-4707. | 2.2 | 2 |
| 15 | Investigation of optical properties of Bi_2GeO_7 sillenite crystals by spectroscopic ellipsometry and Raman spectroscopy. <i>Ceramics International</i> , 2020, 46, 12905-12910. | 4.8 | 14 |
| 16 | The effect of Ga/In ratio and annealing temperature on the nonlinear absorption behaviors in amorphous $\text{TlGa}_x\text{In}_{(1-x)}\text{S}_2$ ($0 \leq x \leq 1$) chalcogenide thin films. <i>Optics and Laser Technology</i> , 2020, 128, 106230. | 4.6 | 15 |
| 17 | Analysis of temperature-dependent transmittance spectra of $\text{Zn}_{0.5}\text{In}_{0.5}\text{Se}$ (ZIS) thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 9356-9362. | 2.2 | 0 |
| 18 | Traps distribution in sol-gel synthesized ZnO nanoparticles. <i>Materials Letters</i> , 2019, 245, 103-105. | 2.6 | 16 |

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|----|--|-----|-----------|
| 19 | Temperature dependence of band gaps in sputtered SnSe thin films. Journal of Physics and Chemistry of Solids, 2019, 131, 22-26. | 4.0 | 18 |
| 20 | Structural and Optical Properties of Ga ₂ Se ₃ Crystals by Spectroscopic Ellipsometry. Journal of Electronic Materials, 2019, 48, 2418-2422. | 2.2 | 11 |
| 21 | Temperature-dependent band gap characteristics of Bi ₁₂ SiO ₂₀ single crystals. Journal of Applied Physics, 2019, 126, . | 2.5 | 17 |
| 22 | Gd-doped ZnO nanoparticles: Synthesis, structural and thermoluminescence properties. Journal of Luminescence, 2019, 207, 220-225. | 3.1 | 37 |
| 23 | Structural and temperature-dependent optical properties of thermally evaporated CdS thin films. Materials Science in Semiconductor Processing, 2019, 93, 148-152. | 4.0 | 37 |
| 24 | Determination of Trapping Parameters of Tl ₂ In ₂ S ₃ Se Layered Single Crystal by Thermoluminescence. Crystal Research and Technology, 2018, 53, 1700134. | 1.3 | 4 |
| 25 | Characterization of defect states in Ga-rich gallium arsenide crystals by thermally stimulated current. Iranian Journal of Science and Technology, Transaction A: Science, 2018, 42, 947-950. | 1.5 | 1 |
| 26 | Study of vibrational modes in Cu _x Ag _{1-x} In ₅ S ₈ mixed crystals by infrared reflection measurements. Indian Journal of Physics, 2018, 92, 431-435. | 1.8 | 0 |
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| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 37 | Thermoluminescence properties of ZnO nanoparticles in the temperature range 10–300 K. Journal of Sol-Gel Science and Technology, 2016, 78, 76-81. | 2.4 | 7 |
| 38 | Low-temperature thermoluminescence study of GaSe:Mn layered single crystals. Philosophical Magazine, 2016, 96, 112-121. | 1.6 | 2 |
| 39 | Optical characterization of CuIn ₅ S ₈ crystals by ellipsometry measurements. Journal of Physics and Chemistry of Solids, 2016, 91, 13-17. | 4.0 | 6 |
| 40 | Optical characterization of Ga ₂ Se ₃ layered crystals by transmission, reflection and ellipsometry. Modern Physics Letters B, 2015, 29, 1550088. | 1.9 | 3 |
| 41 | Thermally assisted variable range hopping in Tl ₄ S ₃ Se crystal. Bulletin of Materials Science, 2015, 38, 593-598. | 1.7 | 9 |
| 42 | Energy Band Diagram and Current Transport Mechanism In p-MgO/n-Ga ₄ Se ₃ S. IEEE Transactions on Electron Devices, 2015, 62, 102-106. | 3.0 | 7 |
| 43 | Band gap and refractive index tunability in thallium based layered mixed crystals. Journal of Applied Physics, 2015, 118, 035701. | 2.5 | 6 |
| 44 | Analysis of glow curve of Ga _{0.5} Se _{0.5} single crystals. Journal of Luminescence, 2015, 168, 236-240. | 3.1 | 0 |
| 45 | Ellipsometry study of optical parameters of AgIn ₅ S ₈ crystals. Physica B: Condensed Matter, 2015, 478, 127-130. | 2.7 | 9 |
| 46 | Composition dependence of lattice parameters and band gap energies of thallium based layered mixed crystals. Indian Journal of Physics, 2015, 89, 657-661. | 1.8 | 6 |
| 47 | Low temperature thermoluminescence of quaternary thallium sulfide Tl ₄ InGa ₃ S ₈ . Indian Journal of Physics, 2015, 89, 571-576. | 1.8 | 0 |
| 48 | Trapping centers and their distribution in Tl ₂ InGaSe ₄ single crystals by thermally stimulated luminescence. Journal of Materials Science, 2014, 49, 2542-2547. | 3.7 | 5 |
| 49 | Anomalous heating rate dependence of thermoluminescence in Tl ₂ GaInS ₄ single crystals. Journal of Materials Science, 2014, 49, 8294-8300. | 3.7 | 15 |
| 50 | Dielectric and Photo-Dielectric Properties of TlGaSeS Crystals. Bulletin of Materials Science, 2014, 37, 505-509. | 1.7 | 4 |
| 51 | Thermoluminescence properties of Tl ₂ Ga ₂ S ₃ Se layered single crystals. Journal of Applied Physics, 2013, 113, 193510. | 2.5 | 6 |
| 52 | The effect of film thickness, Se/S ratio and annealing temperature on the nonlinear absorption behaviors in amorphous Ga _{1-x} Se _x (0 ≤ x ≤ 1) thin films. Optics Communications, 2013, 288, 107-113. | 2.1 | 17 |
| 53 | Excitation intensity- and temperature-dependent photoluminescence in layered structured Tl ₂ GaInSe ₂ S ₂ crystals. Journal of Applied Physics, 2013, 113, 073504. | 2.5 | 3 |
| 54 | Hall mobility and photoconductivity in TlGaSeS crystals. Journal of Applied Physics, 2013, 113, 023712. | 2.5 | 3 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 55 | Dielectric functions and interband critical points of anisotropic chain structured TlSe single crystals. Journal of Applied Physics, 2012, 112, 083526. | 2.5 | 3 |
| 56 | Spectroscopic ellipsometry study of above-band gap optical constants of layered structured TlGaSe ₂ , TlGaS ₂ and TlInS ₂ single crystals. Physica B: Condensed Matter, 2012, 407, 4193-4197. | 2.7 | 19 |
| 57 | Absorption edge and optical constants of layered structured Tl ₂ Ga ₂ Se ₃ S single crystals. Physica Scripta, 2012, 85, 065701. | 2.5 | 4 |
| 58 | Determination of optical parameters of Ga _{0.75} In _{0.25} Se layered crystals. Crystal Research and Technology, 2012, 47, 530-534. | 1.3 | 7 |
| 59 | Dynamical and passive characteristics of the Ag/TlGaSeS/Ag RF resonators. Crystal Research and Technology, 2012, 47, 615-619. | 1.3 | 6 |
| 60 | The nonlinear and saturable absorption characteristics of Ga _{0.90} In _{0.10} Se and Ga _{0.85} In _{0.15} Se semiconductor crystals and their amorphous thin films. Journal of Optics (United Kingdom), 2011, 13, 075203. | 2.2 | 16 |
| 61 | Temperature- and excitation-dependent photoluminescence in TlGaSeS layered crystals. Journal of Alloys and Compounds, 2011, 509, 4205-4208. | 5.5 | 10 |
| 62 | Characterization of Ag/TlInSe ₂ /Ag structure. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1688-1692. | 1.8 | 1 |
| 63 | Raman scattering in TlInS ₂ xSe ₂ (1-x) layered mixed crystals (0.25 ≤ x ≤ 1): Compositional dependence of the mode frequencies and line widths. Physica B: Condensed Matter, 2011, 406, 3374-3376. | 2.7 | 12 |
| 64 | The effect of thickness and doping on the nonlinear absorption behaviour of IIIA-VIA group amorphous semiconductor thin films. , 2011, , . | | 0 |
| 65 | Influence of photonic excitations on the electrical parameters of TlInS ₂ crystals. Crystal Research and Technology, 2010, 45, 433-438. | 1.3 | 0 |
| 66 | Effect of temperature and isomorphous atom substitution on optical absorption edge of TlInS ₂ xSe ₂ (1-x) mixed crystals (0.25 ≤ x ≤ 1). Crystal Research and Technology, 2010, 45, 525-528. | 1.3 | 16 |
| 67 | Effect of isomorphous atom substitution on the refractive index and oscillator parameters of TlInS ₂ xSe ₂ (1-x) (0.25 ≤ x ≤ 1) layered mixed crystals. Crystal Research and Technology, 2010, 45, 1141-1144. | 1.3 | 6 |
| 68 | DETERMINATION OF TRAPPING CENTER PARAMETERS OF Tl ₂ Ga ₂ S ₃ Se ₂ LAYERED CRYSTALS BY THERMALLY STIMULATED CURRENT MEASUREMENTS. International Journal of Modern Physics B, 2010, 24, 2149-2161. | 2.0 | 8 |
| 69 | Coexistence of Indirect and Direct Optical Transitions, Refractive, Index and Oscillator Parameters in TlGaS ₂ , TlGaSe ₂ , and TlInS ₂ Layered Single Crystals. Journal of the Korean Physical Society, 2010, 57, 164-168. | 0.7 | 24 |
| 70 | Analysis of the Hall effect in TlGaTe ₂ single crystals. Journal of Physics Condensed Matter, 2009, 21, 235802. | 1.8 | 8 |
| 71 | Temperature- and photo-excitation effects on the electrical properties of Tl ₄ Se ₃ S crystals. Journal of Physics Condensed Matter, 2009, 21, 115801. | 1.8 | 7 |
| 72 | Temperature-tuned band gap energy and oscillator parameters of Tl ₂ InGaSe ₄ semiconducting layered single crystals. Crystal Research and Technology, 2009, 44, 322-326. | 1.3 | 8 |

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|----|---|-----|-----------|
| 73 | Shallow trapping center parameters in as-grown AgIn_5S_8 crystals determined by thermally stimulated current measurements. <i>Crystal Research and Technology</i> , 2009, 44, 1267-1271. | 1.3 | 7 |
| 74 | Hole-polar phonon interaction scattering mobility in chain structured $\text{TlSe}_{0.75}\text{S}_{0.25}$ crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 1565-1568. | 1.8 | 1 |
| 75 | Transport and recombination kinetics in TlGaTe_2 crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 2555-2558. | 1.8 | 3 |
| 76 | Thermally stimulated current measurements in as-grown TlGaSeS layered single crystals. <i>Current Applied Physics</i> , 2009, 9, 1278-1282. | 2.4 | 14 |
| 77 | Deep Traps Distribution in TlInS_2 Layered Crystals. <i>Acta Physica Polonica A</i> , 2009, 115, 732-737. | 0.5 | 15 |
| 78 | Determination of carrier effective mass, impurity energy levels, and compensation ratio in $\text{Ga}_4\text{Se}_3\text{S}$ layered crystals by Hall effect measurements. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 1662-1665. | 1.8 | 4 |
| 79 | Temperature and excitation intensity tuned photoluminescence in $\text{Tl}_4\text{GaIn}_3\text{S}_8$ layered single crystals. <i>Crystal Research and Technology</i> , 2008, 43, 514-521. | 1.3 | 5 |
| 80 | TEMPERATURE-TUNED BAND GAP ENERGY AND OSCILLATOR PARAMETERS OF TlInSeS LAYERED SINGLE CRYSTALS. <i>International Journal of Modern Physics B</i> , 2008, 22, 3931-3939. | 2.0 | 11 |
| 81 | Electron-lattice interaction scattering mobility in $\text{Tl}_2\text{InGaSe}_4$ single crystals. <i>Journal of Physics Condensed Matter</i> , 2008, 20, 155204. | 1.8 | 2 |
| 82 | Optoelectronic properties of $\text{Ga}_4\text{Se}_3\text{S}$ -layered single crystals. <i>Physica Scripta</i> , 2008, 78, 015701. | 2.5 | 3 |
| 83 | Trap Distribution in TlInS_2 Layered Crystals from Thermally Stimulated Current Measurements. <i>Journal of the Korean Physical Society</i> , 2008, 52, 367-373. | 0.7 | 16 |
| 84 | Below and above bandgap excited photoluminescence in $\text{Tl}_4\text{InGa}_3\text{S}_8$ layered single crystals. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 456221. | 1.8 | 6 |
| 85 | Study of trapping and recombination centres in $\text{Tl}_2\text{InGaTe}_4$ chain crystals by dark electrical conductivity and photoconductivity measurements. <i>Philosophical Magazine</i> , 2007, 87, 5741-5747. | 1.6 | 0 |
| 86 | Thermal lattice scattering mobility and carrier effective mass in intrinsic $\text{Tl}_2\text{InGaTe}_4$ single crystals. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 156206. | 1.8 | 3 |
| 87 | Dispersive optical constants of $\text{Tl}_2\text{InGaSe}_4$ single crystals. <i>Physica Scripta</i> , 2007, 76, 249-252. | 2.5 | 5 |
| 88 | Dispersive optical constants and temperature tuned band gap energy of $\text{Tl}_2\text{InGa}_4\text{S}$ layered crystals. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 256210. | 1.8 | 9 |
| 89 | Specific features of the optical spectra in $\text{Tl}_2\text{In}_2\text{S}_3\text{Se}$ layered single crystals. <i>Crystal Research and Technology</i> , 2007, 42, 621-625. | 1.3 | 10 |
| 90 | Crystal data and some physical properties of $\text{Tl}_2\text{InGaTe}_4$ crystals. <i>Crystal Research and Technology</i> , 2007, 42, 807-811. | 1.3 | 2 |

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|-----|--|-----|-----------|
| 91 | Refractive index, static dielectric constant, energy band gap and oscillator parameters of Ga ₂ SeS single crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007, 204, 3165-3169. | 1.8 | 13 |
| 92 | Optical Properties of TlGaSeS Layered Single Crystals. <i>Journal of the Korean Physical Society</i> , 2007, 51, 2031. | 0.7 | 27 |
| 93 | Trapping Center Parameters and Optical Absorption in Quaternary Tl ₄ In ₃ GaS ₈ , Tl ₄ InGa ₃ Se ₈ , and Tl ₂ InGa ₄ S Semiconductors. <i>Journal of the Korean Physical Society</i> , 2007, 50, 1104. | 0.7 | 0 |
| 94 | Light illumination effect on the electrical and photovoltaic properties of In ₆ S ₇ crystals. <i>Journal of Physics Condensed Matter</i> , 2006, 18, 4609-4614. | 1.8 | 13 |
| 95 | Determination of trapping center parameters of Tl ₂ InGa ₄ S-layered crystals by thermally stimulated current measurements. <i>Journal of Alloys and Compounds</i> , 2006, 417, 23-28. | 5.5 | 12 |
| 96 | Optical properties of TlInS ₂ layered single crystals near the absorption edge. <i>Journal of Materials Science</i> , 2006, 41, 3569-3572. | 3.7 | 17 |
| 97 | Electron-phonon short-range interactions mobility and p- to n-type conversion in TlGaS ₂ crystals. <i>Crystal Research and Technology</i> , 2006, 41, 174-179. | 1.3 | 21 |
| 98 | Excitation intensity and temperature-dependent photoluminescence and optical absorption in Tl ₄ Ga ₃ InSe ₈ layered crystals. <i>Crystal Research and Technology</i> , 2006, 41, 822-828. | 1.3 | 7 |
| 99 | Thermally stimulated current observation of trapping centers in an undoped Tl ₄ Ga ₃ InSe ₈ layered single crystal. <i>Crystal Research and Technology</i> , 2006, 41, 1100-1105. | 1.3 | 2 |
| 100 | Thermally stimulated currents in layered semiconductor Tl ₄ In ₃ GaS ₈ . <i>Semiconductor Science and Technology</i> , 2006, 21, 1250-1255. | 2.0 | 10 |
| 101 | Visible photoluminescence from chain Tl ₄ In ₃ GaSe ₈ semiconductor. <i>Journal of Physics Condensed Matter</i> , 2006, 18, 6057-6064. | 1.8 | 2 |
| 102 | Electrical and photoconductive properties of GaS _{0.75} Se _{0.25} mixed crystals. <i>Crystal Research and Technology</i> , 2005, 40, 253-258. | 1.3 | 8 |
| 103 | Temperature dependence of Raman-active mode frequencies and linewidths in TlGaSe ₂ layered crystals. <i>Crystal Research and Technology</i> , 2005, 40, 264-270. | 1.3 | 15 |
| 104 | Compositional dependence of the Raman lineshapes in GaS _x Se _{1-x} layered mixed crystals. <i>Journal of Raman Spectroscopy</i> , 2005, 36, 879-883. | 2.5 | 7 |
| 105 | Temperature Dependence of Raman-Active Mode Frequencies and Linewidths in TlGaSe ₂ Crystals.. <i>ChemInform</i> , 2005, 36, no. | 0.0 | 0 |
| 106 | Electrical and Photoconductive Properties of GaS _{0.75} Se _{0.25} Mixed Crystals.. <i>ChemInform</i> , 2005, 36, no. | 0.0 | 0 |
| 107 | Optoelectronic and electrical properties of TlGaS ₂ single crystal. <i>Physica Status Solidi A</i> , 2005, 202, 2501-2507. | 1.7 | 21 |
| 108 | Temperature effect on dark electrical conductivity, Hall coefficient, space charge limited current and photoconductivity of TlGaS ₂ single crystals. <i>Semiconductor Science and Technology</i> , 2005, 20, 446-452. | 2.0 | 20 |

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|-----|--|-----|-----------|
| 109 | Electrical conductivity and Hall mobility in p-type TlGaSe ₂ crystals. Materials Research Bulletin, 2004, 39, 1351-1357. | 5.2 | 25 |
| 110 | Thermally stimulated currents in layered Ga ₄ Se ₃ S semiconductor. Physica Status Solidi A, 2004, 201, 2980-2985. | 1.7 | 7 |
| 111 | Investigation of carrier scattering mechanisms in TlInS ₂ single crystals by Hall effect measurements. Crystal Research and Technology, 2004, 39, 439-447. | 1.3 | 18 |
| 112 | Infrared photoluminescence from TlGaS ₂ layered single crystals. Crystal Research and Technology, 2004, 39, 800-806. | 1.3 | 10 |
| 113 | Anharmonic line shift and linewidth of the Raman modes in TlInS ₂ layered crystals. Journal of Raman Spectroscopy, 2004, 35, 55-60. | 2.5 | 13 |
| 114 | Photoelectronic and Electrical Properties of CuIn ₅ S ₈ Single Crystals.. ChemInform, 2004, 35, no. | 0.0 | 0 |
| 115 | Trapping center parameters of TlGaSe ₂ layered crystals. Physica B: Condensed Matter, 2004, 344, 249-254. | 2.7 | 23 |
| 116 | Trap levels in layered semiconductor Ga ₂ SeS. Solid State Communications, 2004, 132, 857-861. | 1.9 | 12 |
| 117 | Hall effect, space-charge limited current and photoconductivity measurements on TlGaSe ₂ layered crystals. Semiconductor Science and Technology, 2004, 19, 505-509. | 2.0 | 30 |
| 118 | Trapping centers in undoped GaS layered single crystals. Applied Physics A: Materials Science and Processing, 2003, 77, 603-606. | 2.3 | 16 |
| 119 | Effect of crystal disorder on linewidth of the Raman modes in GaS _{1-x} Se _x layered mixed crystals. Crystal Research and Technology, 2003, 38, 962-967. | 1.3 | 5 |
| 120 | Photoelectronic and electrical properties of CuIn ₅ S ₈ single crystals. Crystal Research and Technology, 2003, 38, 1063-1070. | 1.3 | 28 |
| 121 | Trap levels in layered semiconductor TlInS _{1.9} Se _{0.1} . Physica Status Solidi A, 2003, 196, 422-428. | 1.7 | 5 |
| 122 | Effect of B ₂ O ₃ addition on the formation and properties of Tl-2212 and Tl-2223 superconductors. Physica Status Solidi A, 2003, 199, 272-276. | 1.7 | 9 |
| 123 | Photoelectronic, optical and electrical properties of TlInS ₂ single crystals. Physica Status Solidi A, 2003, 199, 277-283. | 1.7 | 20 |
| 124 | Thermally stimulated current analysis of shallow levels in TlGaS ₂ layered single crystals. Semiconductor Science and Technology, 2003, 18, 834-838. | 2.0 | 38 |
| 125 | Photoelectronic and electrical properties of InS crystals. Semiconductor Science and Technology, 2002, 17, 1288-1292. | 2.0 | 5 |
| 126 | Temperature- and excitation intensity-dependent photoluminescence in TlInSeS single crystals. Journal of Physics Condensed Matter, 2002, 14, 13685-13692. | 1.8 | 21 |

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|-----|--|-----|-----------|
| 127 | Anharmonicity of Zone-Center Optical Phonons: Raman Scattering Spectra of GaSe _{0.5} Se _{0.5} Layered Crystal. <i>Physica Scripta</i> , 2002, 65, 534-538. | 2.5 | 6 |
| 128 | Temperature-dependent Raman scattering spectra of $\hat{\mu}$ -GaSe layered crystal. <i>Materials Research Bulletin</i> , 2002, 37, 169-176. | 5.2 | 24 |
| 129 | Investigation of Localized Levels in GaS _{0.5} Se _{0.5} Layered Crystals by Means of Electrical, Space-Charge Limited Current and Photoconductivity Measurements. <i>Physica Status Solidi A</i> , 2002, 194, 81-88. | 1.7 | 15 |
| 130 | Low-Temperature Raman Scattering Spectra of GaSexS _{1-x} Layered Mixed Crystals. <i>Crystal Research and Technology</i> , 2002, 37, 1011-1017. | 1.3 | 7 |
| 131 | Carrier Transport Properties of InS Single Crystals. <i>Crystal Research and Technology</i> , 2002, 37, 1104-1112. | 1.3 | 10 |
| 132 | Indirect nuclear exchange coupling and electronic structure of the chain semiconductor TlSe: A ²⁰³ Tl and ²⁰⁵ Tl NMR study. <i>Physical Review B</i> , 2001, 63, . | 3.2 | 16 |
| 133 | Resonant Raman Scattering near the Free-to-Bound Transition in Undoped p-GaSe. <i>Crystal Research and Technology</i> , 2001, 36, 1393. | 1.3 | 1 |
| 134 | Crystal Data, Photoconductivity and Carrier Scattering Mechanisms in CuIn ₅ S ₈ Single Crystals. <i>Crystal Research and Technology</i> , 2001, 36, 1399. | 1.3 | 19 |
| 135 | Effect of lithium doping on the properties of Tl-based superconductors. <i>Superconductor Science and Technology</i> , 2001, 14, 738-740. | 3.5 | 9 |
| 136 | Low-temperature visible photoluminescence spectra of TlGaSe ₂ layered crystal. <i>Journal of Luminescence</i> , 2000, 86, 39-43. | 3.1 | 26 |
| 137 | Temperature dependence of the first-order Raman scattering in GaS layered crystals. <i>Solid State Communications</i> , 2000, 116, 147-151. | 1.9 | 39 |
| 138 | Critical currents in Bi-2223 tapes near T_c under magnetic field and $\hat{\beta}$ -irradiation. <i>Superconductor Science and Technology</i> , 2000, 13, 1625-1628. | 3.5 | 4 |
| 139 | Effect of magnetic field and gamma irradiation on the electrical properties and structure of the Tl-based ceramic superconductors. <i>Superconductor Science and Technology</i> , 2000, 13, 161-164. | 3.5 | 12 |
| 140 | Donor-acceptor pair recombination in gallium sulfide. <i>Journal of Applied Physics</i> , 2000, 88, 7144-7149. | 2.5 | 53 |
| 141 | Voltage-current characteristics of the thallium-based ceramic superconductors. <i>Superconductor Science and Technology</i> , 1999, 12, 592-596. | 3.5 | 8 |
| 142 | Temperature dependence of the Raman-active phonon frequencies in indium sulfide. <i>Solid State Communications</i> , 1999, 110, 231-236. | 1.9 | 27 |
| 143 | Donor-acceptor pair recombination in AgIn ₅ S ₈ single crystals. <i>Journal of Applied Physics</i> , 1999, 85, 3198-3201. | 2.5 | 45 |
| 144 | Radiative donor-acceptor pair recombination in TlInS ₂ single crystals. <i>Semiconductor Science and Technology</i> , 1999, 14, 599-603. | 2.0 | 34 |

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|-----|--|-----|-----------|
| 145 | Structural and Electrical Characterization of Ag ₃ Ga ₅ Te ₉ and Ag ₃ In ₅ Se ₉ Crystals. Crystal Research and Technology, 1998, 33, 923-928. | 1.3 | 10 |
| 146 | Low-temperature photoluminescence spectra of layered semiconductor TlGaS ₂ . Solid State Communications, 1998, 105, 21-24. | 1.9 | 22 |
| 147 | Dependence of the photoluminescence of Tl ₂ InGaS ₄ layered crystal on temperature and excitation intensity. Solid State Communications, 1998, 108, 525-530. | 1.9 | 13 |
| 148 | Low-temperature photoluminescence spectra of InS single crystals. Solid State Communications, 1997, 101, 797-799. | 1.9 | 21 |
| 149 | Crystal Data, Electrical Resistivity and Mobility in Cu ₃ In ₅ Se ₉ and Cu ₃ In ₅ Te ₉ Single Crystals. Crystal Research and Technology, 1997, 32, 395-400. | 1.3 | 23 |
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